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Dual NPN General Purpose Amplifier Transistor

EMX2DXV6T5

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SOT–563 package which is designed for low power surface mount applications, where board space is at a premium.

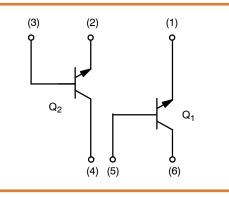
Features

- Reduces Board Space
- High h_{FE}, 210–460 (Typical)
- Low V_{CE(sat)}, < 0.5 V
- These are Pb-Free Devices

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	60	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	50	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	7.0	Vdc
Collector Current – Continuous	۱ _C	100	mAdc

DUAL NPN GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT



MARKING DIAGRAM



3R = Specific Device Code M = Month Code

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
EMX2DXV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel
EMX2DXV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Мах	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	PD	357 (Note 1) 2.9 (Note 1)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	350 (Note 1)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Мах	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D	500 (Note 1) 4.0 (Note 1)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	250 (Note 1)	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 @ Minimum Pad

EMX2DXV6T5

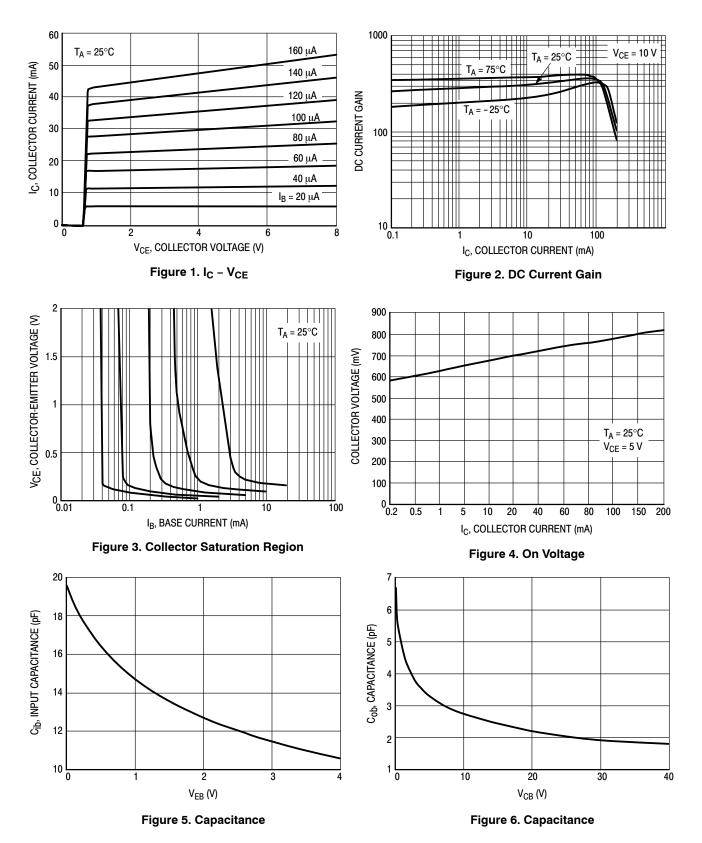
ELECTRICAL CHARACTERISTICS (T_A = 25° C)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage ($I_C = 50 \ \mu Adc, I_E = 0$)	V _(BR) CBO	60	-	-	Vdc
Collector-Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V _(BR) CEO	50	-	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 50 \ \mu Adc, I_E = 0$)	V _{(BR)EBO}	7.0	-	-	Vdc
Collector-Base Cutoff Current ($V_{CB} = 60 \text{ Vdc}, I_E = 0$)	I _{CBO}	-	-	0.5	μΑ
Emitter-Base Cutoff Current $(V_{EB} = 7.0 \text{ Vdc}, I_B = 0)$	I _{EBO}	-	-	0.5	μΑ
Collector-Emitter Saturation Voltage (Note 2) $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	V _{CE(sat)}	-	_	0.4	Vdc
DC Current Gain (Note 3) (V _{CE} = 6.0 Vdc, I _C = 1.0 mAdc)	h _{FE}	120	-	560	-
Transition Frequency (V _{CE} = 12 Vdc, I _C = 2.0 mAdc, f = 30 MHz)	fT	-	180	-	MHz
Output Capacitance (V_{CB} = 12 Vdc, I_C = 0 Adc, f = 1 MHz)	C _{OB}	-	2.0	-	pF

2. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint. 3. Pulse Test: Pulse Width \leq 300 µs, D.C. \leq 2%.

EMX2DXV6T5

TYPICAL ELECTRICAL CHARACTERISTICS



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MILLIMETERS

NDM.

0.55

0.22

0.13

1.60

1.20

0.50 BSC

0.20

1.60

MAX.

0.60

0.27

0.18

1.70

1.30

0.30

1.70

SIDE VIEW

MIN.

0.50

0.17

0.08

1.50

1.10

0.10

1.50

DIM

Α

b

С

D E

e L

 H_E



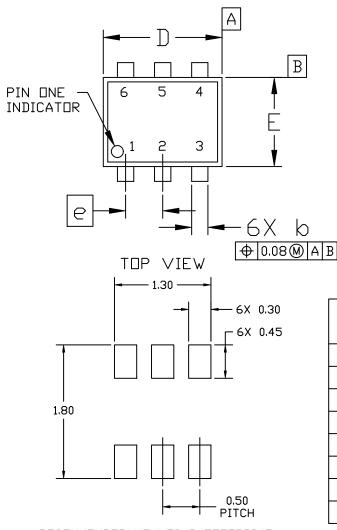


SOT-563, 6 LEAD CASE 463A ISSUE H

DATE 26 JAN 2021

ALE 4:1

- NDTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 1. DIMENSIONING AND TOLERANCING PER A 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS DF BASE MATERIAL.



RECOMMENDED MOUNTING FOOTPRINT* * For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

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STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. EMITTER 1	PIN 1. EMITTER 1	PIN 1. CATHIDE 1
2. BASE 1	2. EMITTER 2	2. CATHIDE 1
3. COLLECTOR 2	3. BASE 2	3. ANUDE/ANUDE 2
4. EMITTER 2	4. COLLECTOR 2	4. CATHIDE 2
5. BASE 2	5. BASE 1	5. CATHIDE 2
6. COLLECTOR 1	6. COLLECTOR 1	6. ANUDE/ANUDE 1
STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. COLLECTOR	PIN 1. CATHEDE	PIN 1. CATHODE
2. COLLECTOR	2. CATHEDE	2. ANODE
3. BASE	3. ANEDE	3. CATHODE
4. EMITTER	4. ANEDE	4. CATHODE
5. COLLECTOR	5. CATHEDE	5. CATHODE
6. COLLECTOR	6. CATHEDE	6. CATHODE
STYLE 7:	STYLE 8:	STYLE 9:
PIN 1. CATHODE	PIN 1. DRAIN	PIN 1. SDURCE 1
2. ANODE	2. DRAIN	2. GATE 1
3. CATHODE	3. GATE	3. DRAIN 2
4. CATHODE	4. SDURCE	4. SDURCE 2
5. ANODE	5. DRAIN	5. GATE 2
6. CATHODE	6. DRAIN	6. DRAIN 1
STYLE 10: PIN 1. CATHODE 1 2. N/C 3. CATHODE 2 4. ANODE 2 5. N/C 6. ANODE 1	STYLE 11: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	

6. COLLECTOR 2

DATE 26 JAN 2021

GENERIC **MARKING DIAGRAM***



XX = Specific Device Code

M = Month Code

. = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-563, 6 LEAD		PAGE 2 OF 2	

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